

Thomas Frost

List of Publications by Year in descending order

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papers

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623734

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39
all docs

39
docs citations

39
times ranked

1294
citing authors

#	ARTICLE	IF	CITATIONS
1	Monolithic Electrically Injected Nanowire Array Edge-Emitting Laser on (001) Silicon. Nano Letters, 2014, 14, 4535-4541.	9.1	177
2	Room Temperature Electrically Injected Polariton Laser. Physical Review Letters, 2014, 112, 236802.	7.8	173
3	An enhanced surface passivation effect in InGaN/GaN disk-in-nanowire light emitting diodes for mitigating Shockley-Read-Hall recombination. Nanoscale, 2015, 7, 16658-16665.	5.6	84
4	Electrically pumped single-photon emission at room temperature from a single InGaN/GaN quantum dot. Applied Physics Letters, 2014, 105, .	3.3	83
5	InGaN/GaN Quantum Dot Red $(\lambda=630\text{--}650\text{ nm})$ Laser. IEEE Journal of Quantum Electronics, 2013, 49, 923-931.	1.9	65
6	Formation and Nature of InGaN Quantum Dots in GaN Nanowires. Nano Letters, 2015, 15, 1647-1653.	9.1	58
7	Room-Temperature Spin Polariton Diode Laser. Physical Review Letters, 2017, 119, 067701.	7.8	34
8	Continuous-wave operation and differential gain of InGaN/GaN quantum dot ridge waveguide lasers ($\lambda=420\text{ nm}$) on c-plane GaN substrate. Applied Physics Letters, 2012, 101, 041108.	3.3	30
9	High performance red-emitting multiple layer InGaN/GaN quantum dot lasers. Japanese Journal of Applied Physics, 2016, 55, 032101.	1.5	30
10	Small signal modulation characteristics of red-emitting ($\lambda = 610\text{ nm}$) III-nitride nanowire array lasers on (001) silicon. Applied Physics Letters, 2015, 106, .	3.3	29
11	Room Temperature GaN-Based Edge-Emitting Spin-Polarized Light Emitting Diode. IEEE Photonics Technology Letters, 2017, 29, 338-341.	2.5	18
12	Small-signal modulation and differential gain of red-emitting ($\lambda=630\text{ nm}$) InGaN/GaN quantum dot lasers. Applied Physics Letters, 2013, 103, .	3.3	17
13	Characteristics of a high speed $1.22\lambda/4\text{m}$ tunnel injection p-doped quantum dot excited state laser. Applied Physics Letters, 2011, 98, 011103.	3.3	15
14	GaAs-based high temperature electrically pumped polariton laser. Applied Physics Letters, 2014, 104, .	3.3	15
15	Output polarization characteristics of a GaN microcavity diode polariton laser. Physical Review B, 2016, 94, .	3.2	13
16	Red and Near-Infrared III-Nitride Quantum Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-9.	2.9	12
17	Physical model for high indium content InGaN/GaN self-assembled quantum dot ridge-waveguide lasers emitting at red wavelengths ($\lambda \sim 630\text{ nm}$). Optics Express, 2015, 23, 12850.	3.4	11
18	InGaN/GaN self-organized quantum dot lasers grown by molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 566-570.	1.5	10

#	ARTICLE	IF	CITATIONS
19	Temperature-dependent measurement of Auger recombination in $\text{In}_{0.40}\text{Ga}_{0.60}\text{N}/\text{GaN}$ red-emitting ($\lambda = 630\text{ nm}$) quantum dots. <i>Applied Physics Letters</i> , 2014, 104, 081121.	3.3	10
20	Optical constants of $\text{In}_x\text{Ga}_{1-x}\text{N}$ ($0 \leq x \leq 0.73$) in the visible and near-infrared wavelength regimes. <i>Optics Letters</i> , 2015, 40, 3304.	3.3	9
21	The role of defects in lowering the effective polariton temperature in electric and optically pumped polariton lasers. <i>Applied Physics Letters</i> , 2016, 108, 041102.	3.3	9
22	Detailed model for the $\text{In}_{0.18}\text{Ga}_{0.82}\text{N}/\text{GaN}$ self-assembled quantum dot active material for $\lambda = 420\text{ nm}$ emission. <i>Optics Express</i> , 2014, 22, 22716.	3.4	8
23	Small-signal modulation characteristics of a polariton laser. <i>Scientific Reports</i> , 2015, 5, 11915.	3.3	8
24	Green-Emitting ($\lambda = 525\text{ nm}$) InGaN/GaN Quantum Dot Light Emitting Diodes Grown on Quantum Dot Dislocation Filters. <i>IEEE Journal of Quantum Electronics</i> , 2014, 50, 228-235.	1.9	5
25	A monolithic InGaN/GaN disk-in-nanowire electrically pumped edge-emitting green ($\lambda = 533\text{ nm}$) laser on (001) silicon. , 2014, , .		3
26	Red-emitting InGaN/GaN quantum dot laser. , 2013, , .		2
27	Ridge waveguide InGaN/GaN quantum dot edge emitting visible lasers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 816-819.	0.8	2
28	InGaN/GaN nanowire LEDs and lasers. , 2016, , .		2
29	Room temperature strong coupling effects and polariton lasing under electrical injection. , 2014, , .		1
30	High temperature stability in integrable quantum dot lasers with dry etched mirror facets for on-chip optical interconnects. , 2011, , .		0
31	Monolithic integration of passive components with high performance quantum dot lasers. , 2012, , .		0
32	InGaN/GaN quantum dot lasers. , 2013, , .		0
33	Room temperature electrically injected $\text{In}_{0.4}\text{Ga}_{0.6}\text{N}/\text{GaN}$ quantum-dot visible ($\lambda = 620\text{ nm}$) single photon source. , 2014, , .		0
34	$0.5\text{--}1.3\ \mu\text{m}$ III-nitride lasers and light emitting diodes epitaxially grown on (001) silicon. , 2015, , .		0
35	High performance $\text{InGaN}/(\text{In})\text{GaN}$ quantum dot ($\lambda = 630\text{ nm}$) lasers. , 2015, , .		0
36	Physical model for indium-rich InGaN/GaN self-assembled quantum dot ridge-waveguide lasers emitting		0

#	ARTICLE	IF	CITATIONS
37	High-Speed Electrical Modulation of Polariton Lasers. , 2015, , .		0
38	Linearly and circularly polarized ultraviolet GaN microcavity polariton lasers. , 2016, , .		0